

(19) World Intellectual Property Organization
International Bureau

G00002

(43) International Publication Date
7 February 2002 (07.02.2002)

PCT

(10) International Publication Number
WO 02/09907 A1(51) International Patent Classification⁷: B24B 49/00

(21) International Application Number: PCT/US01/24170

(22) International Filing Date: 31 July 2001 (31.07.2001)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/628,962 31 July 2000 (31.07.2000) US(71) Applicant: SILICON VALLEY GROUP, INC. [US/US];
440 Kings Village Road, Scotts Valley, CA 95066-4081
(US).

(72) Inventors: SAKA, Nannaji; 101 Western Avenue, Apartment #51, Cambridge, MA 02139 (US). LAI, Jiun-Yu; 254 College Farm Road, Waltham, MA 02451 (US). OH, Hilario, L.; 1132 West Avon Road, Rochester Hills, MI 48309 (US).

(74) Agents: SWIATEK, Maria, S. et al.; Flehr Hohbach Test Albritton & Herbert LLP, 4 Embarcadero Center, Suite 3400, San Francisco, CA 94111-4187 (US).

(81) Designated States (*national*): AE, AG, AI., AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZW.(84) Designated States (*regional*): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

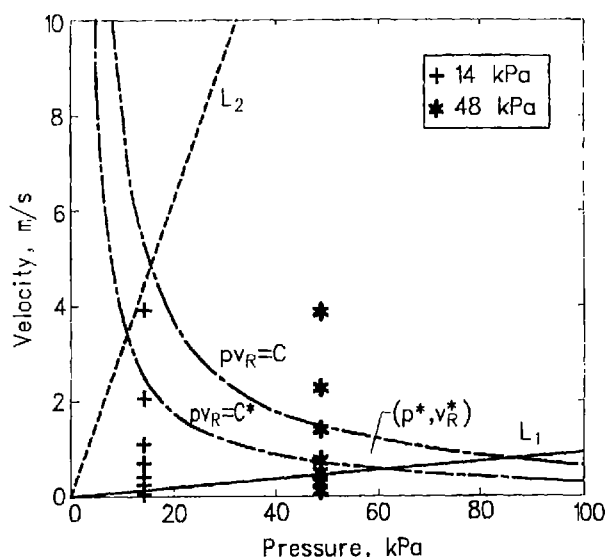
— with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: METHOD OF CHEMICAL MECHANICAL POLISHING



162162



(57) Abstract: In the Chemical Mechanical Polishing (CMP) process employed for microelectronics manufacturing, three contact regimes between the wafer surface and the polishing pad may be proposed: direct contact, mixed or partial contact, and hydroplaning. However, an effective *in situ* method for characterizing the wafer/pad contact and a systematic way of relating contact conditions to the process parameters are still lacking. In this work, the interfacial friction force, measured by a load sensor on the wafer carrier, has been employed to characterize the contact conditions. Models that relate the friction coefficient to the applied pressure, relative velocity, and slurry viscosity are developed and verified by experiments. Additionally, a correlation between friction coefficient and the material removal rate (MRR) is established and the effects of process parameters on the Preston constant are investigated.